

TITLE: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE
GATE
INVENTORS NAME: Leonard Forbes et al.
DOCKET NO.: 303.355US4

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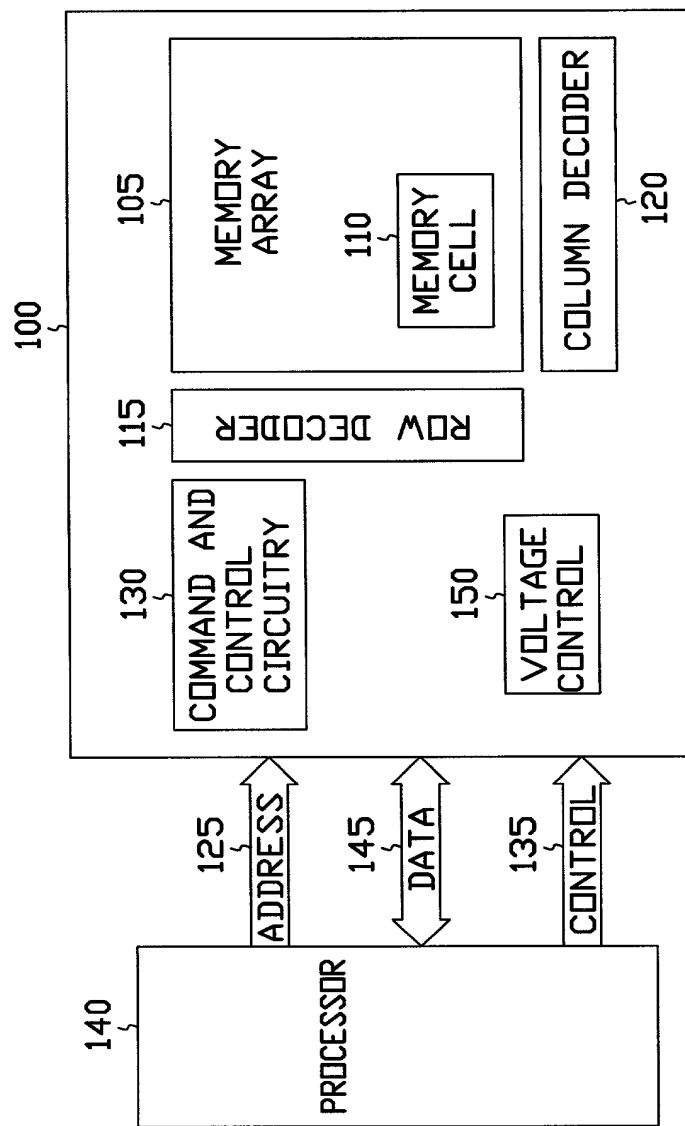


FIG. 1

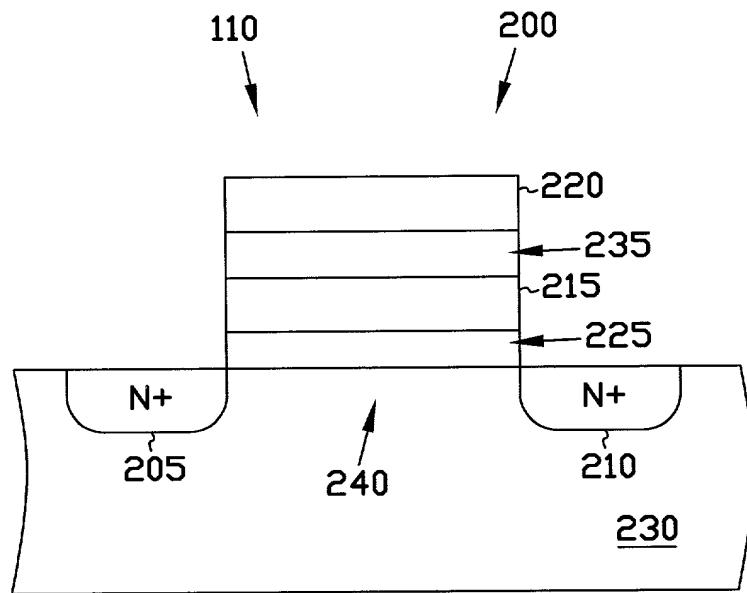


FIG. 2

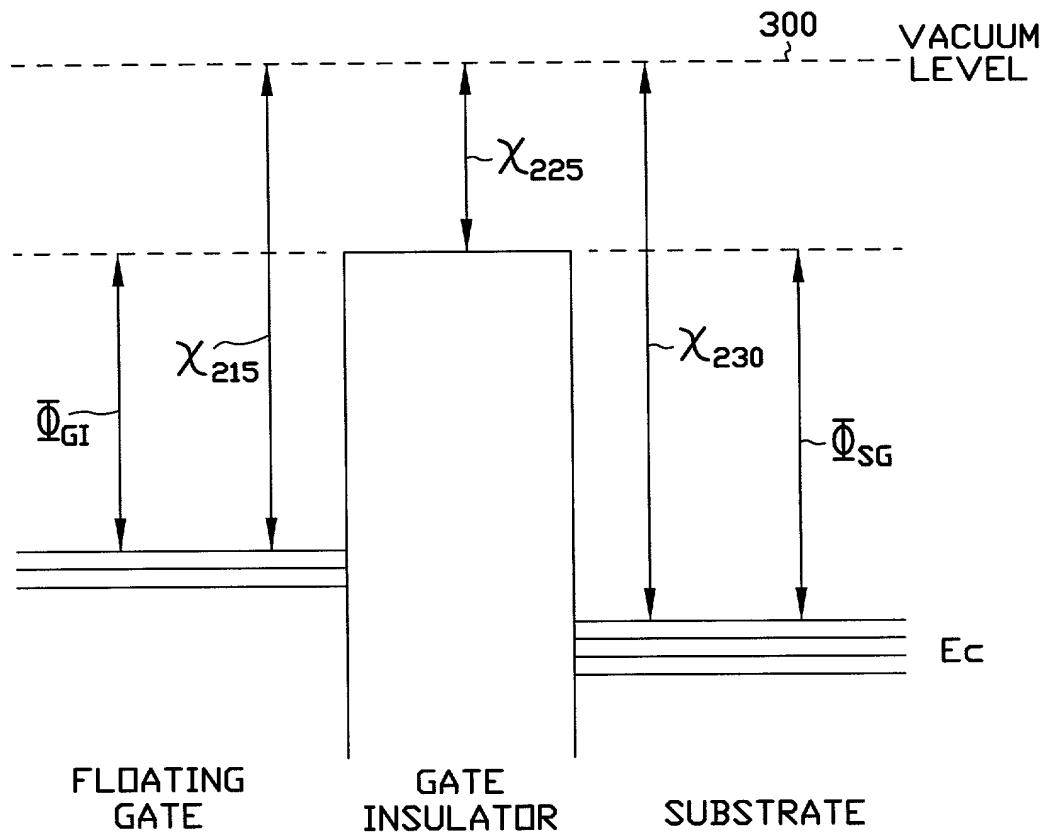


FIG. 3

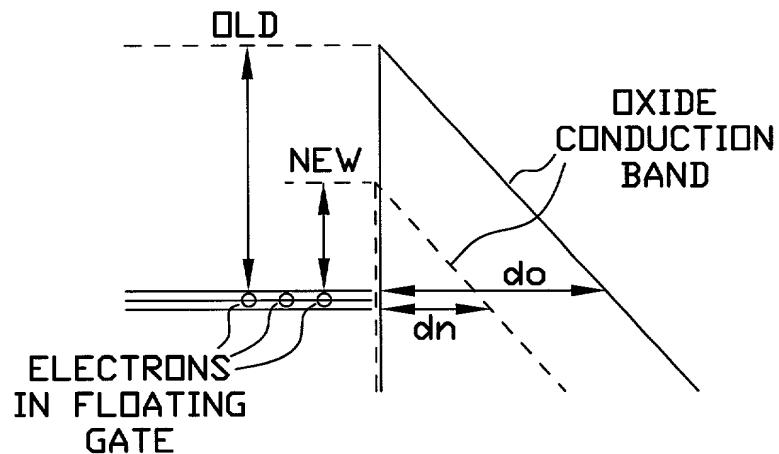


FIG. 4

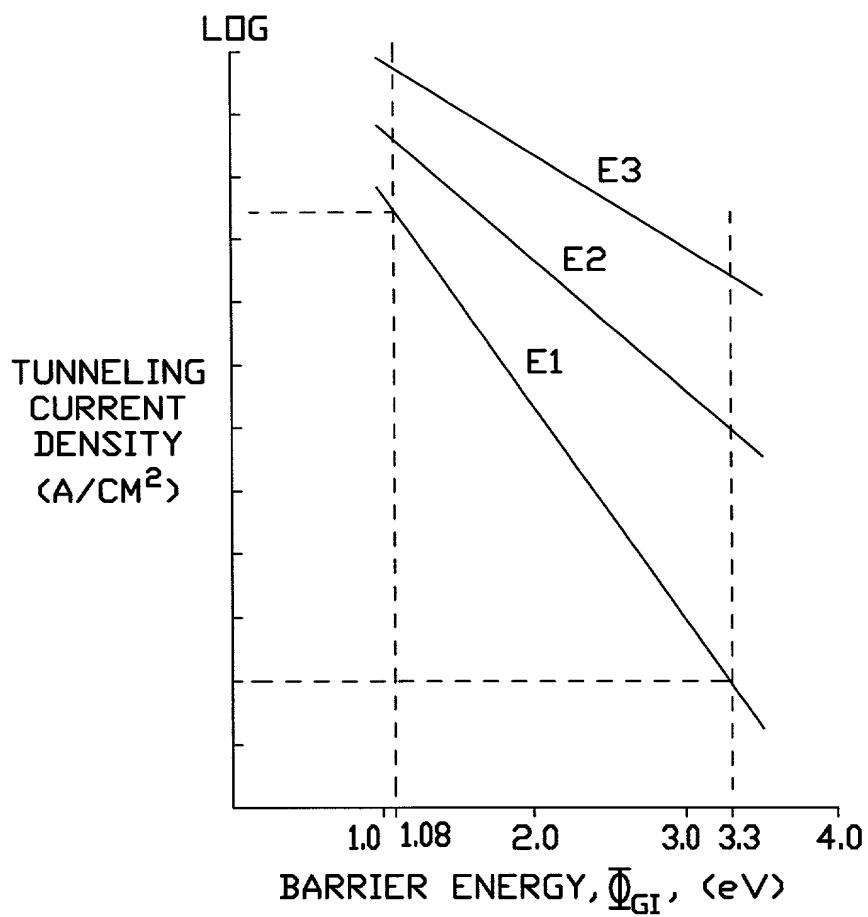


FIG. 5

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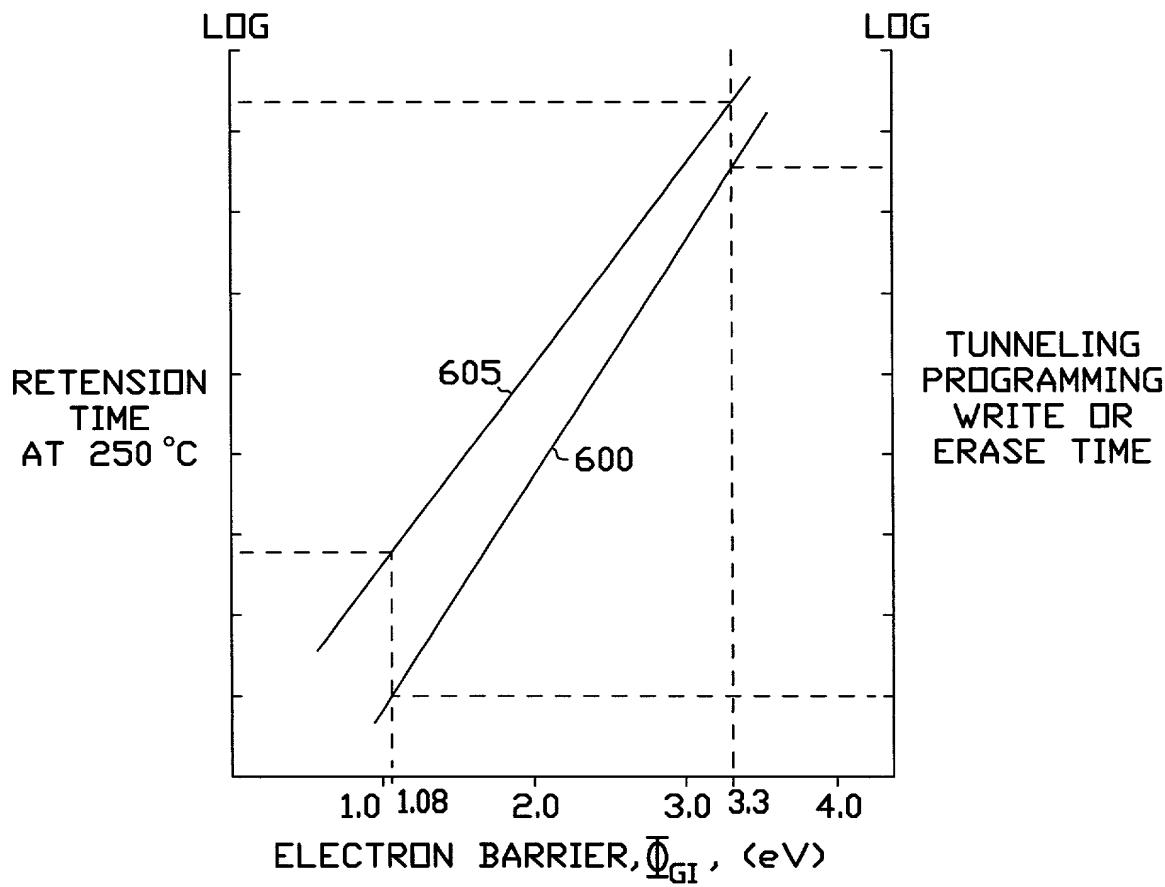


FIG. 6

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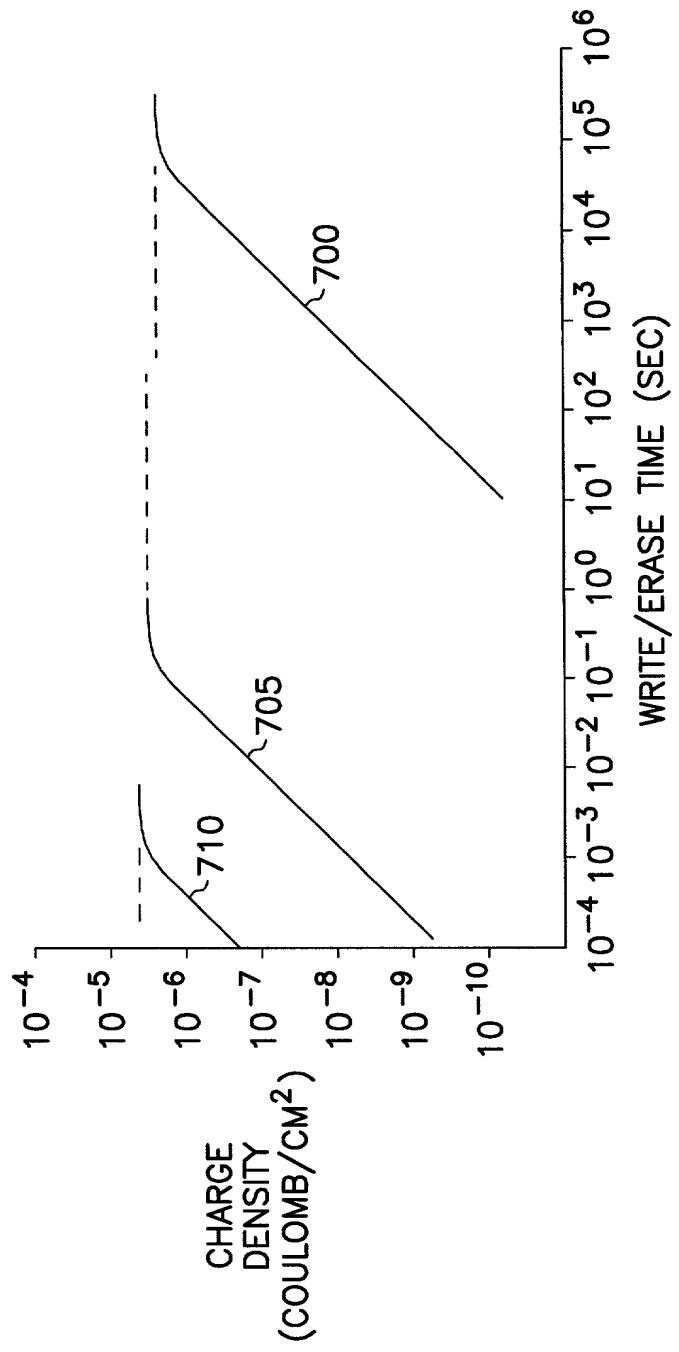


FIG. 7

TITLE: DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
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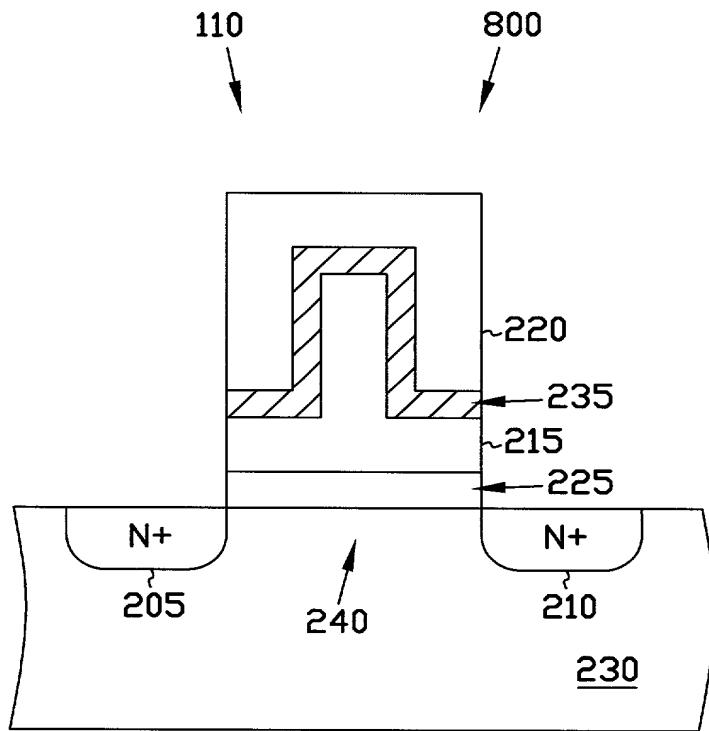


FIG. 8

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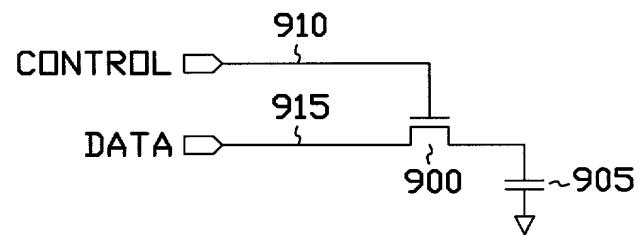


FIG. 9A (PRIOR ART)

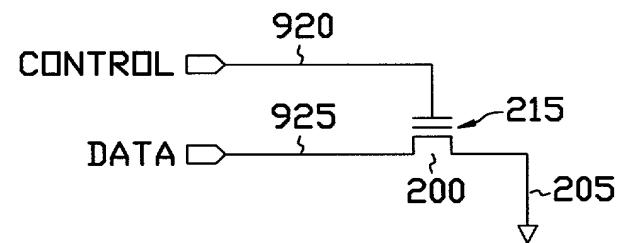


FIG. 9B